

Shin-Ichi Kanemaru

List of Publications by Year in descending order

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141
papers

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279487

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344852

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142
all docs

142
docs citations

142
times ranked

1028
citing authors

#	ARTICLE	IF	CITATIONS
1	Demonstration, Analysis, and Device Design Considerations for Independent DG MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 2046-2053.	1.6	115
2	Highly suppressed short-channel effects in ultrathin SOI n-MOSFETs. IEEE Transactions on Electron Devices, 2000, 47, 354-359.	1.6	103
3	Fabrication of double-gated Si field emitter arrays for focused electron beam generation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1968.	1.6	99
4	Destiny of Autologous Bone Marrow-Derived Stromal Cells Implanted in the Vocal Fold. Annals of Otolaryngology, Rhinology and Laryngology, 2005, 114, 907-912.	0.6	78
5	Emission statistics for Si and HfC emitter arrays after residual gas exposure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 707.	1.6	73
6	Fabrication and characterization of HfC coated Si field emitter arrays. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1589.	1.6	51
7	Ultrathin Channel Vertical DG MOSFET Fabricated by Using Ion-Bombardment-Retarded Etching. IEEE Transactions on Electron Devices, 2004, 51, 2078-2085.	1.6	50
8	Ultrastable emission from a metal-oxide-semiconductor field-effect transistor-structured Si emitter tip. Applied Physics Letters, 1996, 69, 1577-1578.	1.5	49
9	Control of emission currents from silicon field emitter arrays using a built-in MOSFET. Applied Surface Science, 1997, 111, 218-223.	3.1	46
10	Air-bridge-structured silicon nanowire and anomalous conductivity. Applied Physics Letters, 1999, 75, 3986-3988.	1.5	39
11	Control of emission characteristics of silicon field emitter arrays by an ion implantation technique. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 1885.	1.6	37
12	Fabrication and characterization of lateral field-emitter triodes. IEEE Transactions on Electron Devices, 1991, 38, 2334-2336.	1.6	35
13	Fabrication of a New Si Field Emitter Tip with Metal-Oxide-Semiconductor Field-Effect Transistor (MOSFET) Structure. Japanese Journal of Applied Physics, 1996, 35, 6637-6640.	0.8	34
14	A New Metal-Oxide-Semiconductor Field-Effect-Transistor-Structured Si Field Emitter Tip. Japanese Journal of Applied Physics, 1996, 35, L861-L863.	0.8	31
15	Fabrication of Silicon Field Emitter Arrays Integrated with Beam Focusing Lens. Japanese Journal of Applied Physics, 1996, 35, 6626-6628.	0.8	30
16	Beam focusing characteristics of silicon microtips with an in-plane lens. IEEE Transactions on Electron Devices, 1997, 44, 498-502.	1.6	30
17	Emission Characteristics of Ion-Implanted Silicon Emitter Tips. Japanese Journal of Applied Physics, 1995, 34, 6907-6911.	0.8	29
18	A novel heteroepitaxy method of Ge films on CaF ₂ by electron beam exposure. Journal of Applied Physics, 1988, 63, 1060-1064.	1.1	27

#	ARTICLE	IF	CITATIONS
19	Modeling of field emission nanotriodes with carbon nanotube emitters. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 366.	1.6	27
20	Fabrication of a Field Emitter Array with a Built-in Einzel Lens. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 06FK02.	0.8	26
21	The efficacy of a novel collagen-gelatin scaffold with basic fibroblast growth factor for the treatment of vocal fold scar. <i>Journal of Tissue Engineering and Regenerative Medicine</i> , 2017, 11, 1598-1609.	1.3	26
22	Regeneration of Mastoid Air Cells in Clinical Applications by In Situ Tissue Engineering. <i>Laryngoscope</i> , 2005, 115, 253-258.	1.1	25
23	Emission current saturation of the p-type silicon gated field emitter array. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 3357.	1.6	24
24	Fabrication of Si field emitter arrays integrated with metal-oxide-semiconductor field-effect transistor driving circuits. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 2309.	1.6	24
25	Electron-beam characteristics of double-gated Si field emitter arrays. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996, 14, 1902.	1.6	23
26	Stable emission from a MOSFET-structured emitter tip in poor vacuum. <i>Applied Surface Science</i> , 1999, 146, 198-202.	3.1	23
27	A case of floppy epiglottis in adult: A simple surgical remedy. <i>Auris Nasus Larynx</i> , 2007, 34, 409-411.	0.5	23
28	Biocompatibility and Efficacy of Collagen/Gelatin Sponge Scaffold With Sustained Release of Basic Fibroblast Growth Factor on Vocal Fold Fibroblasts in 3-Dimensional Culture. <i>Annals of Otology, Rhinology and Laryngology</i> , 2015, 124, 116-125.	0.6	23
29	Fabrication of Volcano-Structured Double-Gate Field Emitter Array by Etch-Back Technique. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 5252-5255.	0.8	22
30	Fabrication of an ultrasharp and high-aspect-ratio microprobe with a silicon-on-insulator wafer for scanning force microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995, 13, 331.	1.6	21
31	Emission and focusing characteristics of volcano-structured double-gated field emitter arrays. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 701-704.	1.3	21
32	Characterization of electrical conduction in silicon nanowire by scanning Maxwell-stress microscopy. <i>Applied Physics Letters</i> , 2001, 78, 2560-2562.	1.5	20
33	Room-temperature crystallization of amorphous films by RF plasma treatment. <i>Thin Solid Films</i> , 2009, 517, 3092-3095.	0.8	20
34	Fabrication and Characterization of Comb-Shaped Lateral Field-Emitter Arrays. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 1221-1226.	0.8	19
35	Fabrication of a Nanometer-Scale Si-Wire by Micromachining of a Silicon-on-Insulator Substrate. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 7182-7185.	0.8	19
36	Fabrication and characterization of a nanogap edge emitter with a silicon-on-insulator wafer. <i>Applied Surface Science</i> , 1999, 146, 203-208.	3.1	19

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37	Modeling of Optimized Field Emission Nanotriodes with Aligned Carbon Nanotubes of Variable Heights. Japanese Journal of Applied Physics, 2004, 43, 485-491.	0.8	18
38	HfC field emitter array controlled by built-in poly-Si thin film transistor. Journal of Vacuum Science & Technology B, 2006, 24, 936.	1.3	18
39	Fabrication of Si Field Emitter Tip for a Three-Dimensional Vacuum Magnetic Sensor. Japanese Journal of Applied Physics, 1996, 35, 6629-6631.	0.8	17
40	Fabrication of Metal-Oxide-Semiconductor Field-Effect-Transistor-Structured Silicon Field Emitters with a Polysilicon Dual Gate. Japanese Journal of Applied Physics, 1997, 36, 7736-7740.	0.8	17
41	Emission uniformity improvement of Si field emitter arrays by surface modification. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1581.	1.6	17
42	Microscopic characterization of field emitter array structure and work function by scanning Maxwell-stress microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2105.	1.6	16
43	Focusing Characteristics of Double-Gated Field-Emitter Arrays with a Lower Height of the Focusing Electrode. Applied Physics Express, 0, 1, 053001.	1.1	16
44	Low-voltage operation from the tower structure metal-oxide-semiconductor field-effect transistor Si field emitter. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 588.	1.6	15
45	Fabrication of Polycrystalline Silicon Field Emitter Arrays with Hafnium Carbide Coating for Thin-Film-Transistor Controlled Field Emission Displays. Japanese Journal of Applied Physics, 2004, 43, 3919-3922.	0.8	15
46	Characterization of enhanced field emission from HfC-coated Si emitter arrays through parameter extraction. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1227.	1.6	15
47	Characteristics of Ion-Induced Bending Phenomenon. Japanese Journal of Applied Physics, 2010, 49, 056501.	0.8	15
48	Improvement of the quality of Ge films on CaF ₂ /Si(111) structures by predeposited thin Ge layers. Surface Science, 1986, 174, 666-670.	0.8	14
49	Effects of conduction type on field-electron emission from single Si emitter tips with extraction gate. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1111.	1.6	14
50	Model parameter extraction for nonlinear Fowler-Nordheim field emission data. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1550.	1.6	14
51	Development of Thin-Film Bending Technique Induced by Ion-Beam Irradiation. Applied Physics Express, 2009, 2, 066501.	1.1	14
52	Three-dimensional vacuum magnetic sensor with a Si emitter tip. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1233.	1.6	13
53	Damageless vacuum sealing of Si field emitters with CHF ₃ plasma treatment. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 920.	1.6	13
54	Fabrication of ultrathin Si Channel Wall For Vertical Double-Gate Metal-Oxide-Semiconductor Field-Effect Transistor (DG MOSFET) by Using Ion-Bombardment-Retarded Etching (IBRE). Japanese Journal of Applied Physics, 2003, 42, 1916-1918.	0.8	13

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55	Control of Crystal Orientations in Lattice-Mismatched SrF ₂ and (Ca, Sr)F ₂ Films on Si Substrates by Intermediate CaF ₂ Films. Japanese Journal of Applied Physics, 1985, 24, L56-L58.	0.8	12
56	Suppressed threshold voltage roll-off characteristic of 40 nm gate length ultrathin SOI MOSFET. Electronics Letters, 1998, 34, 2069.	0.5	12
57	Work function controllability of metal gates made by interdiffusing metal stacks with low and high work functions. Microelectronic Engineering, 2005, 80, 284-287.	1.1	12
58	Silicon field emission array as novel charge neutralization device for high current ion implanter. Nuclear Instruments & Methods in Physics Research B, 2005, 237, 390-394.	0.6	12
59	A Novel Electron-Beam Exposure Epitaxy for Growing GaAs Films on Fluoride/Si Structures. Japanese Journal of Applied Physics, 1987, 26, L1834-L1836.	0.8	11
60	Single electron memory characteristic of silicon nanodot nanowire transistor. Electronics Letters, 2000, 36, 1322.	0.5	11
61	Individual tip evaluation in Si field emitter arrays by electrostatic lens projector. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 952.	1.6	11
62	Field emitter array with a memory function for ultrahigh luminance field emission display. Journal of Vacuum Science & Technology B, 2007, 25, 464.	1.3	11
63	Ring-shaped images as a result of nonuniform field emission from capped carbon nanotubes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 649.	1.6	10
64	Low-Operation-Voltage Comb-Shaped Field Emitter Array. Japanese Journal of Applied Physics, 1992, 31, L884-L886.	0.8	9
65	Vacuum Microtriode with Comb-Shaped Lateral Field-Emitter Array. Japanese Journal of Applied Physics, 1993, 32, L809-L812.	0.8	9
66	Electrical Characteristics of Air-Bridge-Structured Silicon Nanowire Fabricated by Micromachining a Silicon-on-Insulator Substrate. Japanese Journal of Applied Physics, 1999, 38, 7237-7240.	0.8	9
67	Optimization of transistor structure for transistor-stabilized field emitter arrays. IEEE Transactions on Electron Devices, 1999, 46, 2261-2264.	1.6	9
68	Emission-uniformity improvement and work-function reduction of Si emitter tips by ethylene gas exposure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1911.	1.6	9
69	Regeneration of mastoid air cells: Clinical applications. Acta Oto-Laryngologica, 2004, 124, 80-84.	0.3	9
70	Work function uniformity of Al-Ni alloys obtained by scanning Maxwell-stress microscopy as an effective tool for evaluating metal transistor gates. Applied Physics Letters, 2005, 86, 094104.	1.5	9
71	Fabrication and characterization of vertical-type, self-aligned asymmetric double-gate metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2005, 86, 123512.	1.5	9
72	A case report of myasthenia gravis localized to the larynx. Auris Nasus Larynx, 2007, 34, 401-403.	0.5	9

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73	A field emitter array with an amorphous silicon thin-film transistor on glass. Applied Physics Letters, 1998, 73, 1301-1303.	1.5	8
74	A field emitter array monolithically integrated with a thin-film transistor on glass for display applications. Applied Surface Science, 1999, 146, 187-192.	3.1	8
75	Fabrication of a vacuum-sealed magnetic sensor with a Si field emitter tip. Journal of Micromechanics and Microengineering, 2001, 11, 81-83.	1.5	8
76	Dual-Gate Electron Emission Structure with Nanotube-on-Emitter for X-Ray Generation. Japanese Journal of Applied Physics, 2002, 41, 5551-5556.	0.8	8
77	CdTe x-ray image sensor using a field emitter array. Journal of Vacuum Science & Technology B, 2009, 27, 725-728.	1.3	8
78	Fabrication of a Three-Dimensional Vacuum Magnetic Sensor with a Si Tip. Japanese Journal of Applied Physics, 1997, 36, 7754-7756.	0.8	7
79	CHF3 Plasma Treatment of Si Field Emitter Arrays For No Damage Vacuum Packaging. Japanese Journal of Applied Physics, 2000, 39, L755-L756.	0.8	7
80	Novel Process for Vertical Double-Gate (DG) Metal-Oxide-Semiconductor Field-Effect-Transistor (MOSFET) Fabrication. Japanese Journal of Applied Physics, 2003, 42, 4138-4141.	0.8	7
81	Tissue engineering for the regeneration of the mastoid air cells: A preliminary in vitro study. Acta Oto-Laryngologica, 2004, 124, 75-79.	0.3	7
82	Scanning tunneling microscopy observations of hafnium carbide thin films as a field emission material. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 741.	1.6	7
83	Growth and Characterization of Compositionally Graded (Ca, Sr)F ₂ Layers on Si(111) Substrates. Japanese Journal of Applied Physics, 1987, 26, 848-851.	0.8	6
84	Amorphous-silicon-on-glass field emitter arrays. IEEE Electron Device Letters, 1996, 17, 261-263.	2.2	6
85	Modeling of Focused Carbon Nanotube Array Emitters for Field-Emission Displays. Japanese Journal of Applied Physics, 2004, 43, 3328-3334.	0.8	6
86	Diagnostics of doping integrity in n ⁺ /p/n ⁺ transistor-channel structure by scanning nonlinear dielectric microscopy. Applied Physics Letters, 2004, 84, 3169-3171.	1.5	6
87	Fabrication of Silicon Field Emitter Arrays with 0.1- μ m-Diameter Gate by Focused Ion Beam Lithography. Japanese Journal of Applied Physics, 1995, 34, 6932-6934.	0.8	5
88	Fabrication of a New Field Emitter Array with a Built-in Thin-Film Transistor on Glass. Japanese Journal of Applied Physics, 1998, 37, 7134-7137.	0.8	5
89	Plane-view observation technique of silicon nanowires by transmission electron microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1897.	1.6	5
90	Fabrication of HfC-Coated Si Field Emitter Arrays with Built-in Poly-Si Thin-Film Transistor. Japanese Journal of Applied Physics, 2005, 44, 5740-5743.	0.8	5

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91	5-Fluorouracil Ointment for the Treatment of Otitis Media With Effusion. <i>Laryngoscope</i> , 2007, 117, 215-219.	1.1	5
92	Regenerative Treatment for Soft Tissue Defects of the External Auditory Meatus. <i>Otology and Neurotology</i> , 2014, 35, 442-448.	0.7	5
93	Nanoscale Evaluation of Structure and Surface Potential of Gated Field Emitters by Scanning Maxwell-Stress Microscope. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 6912.	0.8	4
94	A MOSFET-structured Si tip for stable emission current. , 0, , .		4
95	Fabrication of Field Emitter Arrays with Hydrogenated Amorphous Silicon on Glass. <i>Japanese Journal of Applied Physics</i> , 1996, 35, 6620-6622.	0.8	4
96	Fabrication technology of ultrafine SiO ₂ masks and Si nanowires using oxidation of vertical sidewalls of a poly-Si layer. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999, 17, 77.	1.6	4
97	Improvement of electron emission characteristics of Si field emitter arrays by surface modification. <i>Applied Surface Science</i> , 1999, 146, 172-176.	3.1	4
98	Mechanism of Tungsten Plug Corrosion during Chemical Stripping Process: Scanning Maxwell-Stress Microscopy and Electrochemical Potentiometry Studies. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 5108-5112.	0.8	4
99	Demonstration of threshold voltage control techniques for vertical-type 4-terminal double-gate MOSFETs (4T-DGFET). , 0, , .		4
100	Parameter dispersion characterization for arrays of HfC-coated emitters on poly-Si substrate. <i>Journal of Vacuum Science & Technology B</i> , 2006, 24, 1045.	1.3	4
101	Fabrication of Petal-Shaped Vertical Field Emitter Arrays. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 6916-6921.	0.8	3
102	Fabrication of 40-nm Gate Length Ultrathin n-MOSFETs Using Epitaxial Layer Transfer SOI Wafers. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2492-2495.	0.8	3
103	Doping diagnosis by evaluation of the surface Fermi level using scanning Maxwell-stress microscopy. <i>Applied Physics Letters</i> , 2003, 82, 2166-2168.	1.5	3
104	Silicon nanowire with programmable conductivity analyzed by scanning Maxwell-stress microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 664.	1.6	3
105	Metal-oxide-semiconductor field-effect transistor-structured Si field emitter array with a built-in ring gate lens. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2003, 21, 495.	1.6	3
106	Stabilization technique for columella using trimmed autologous temporal fascia in type III and IV tympanoplasty – muffler method. <i>Acta Oto-Laryngologica</i> , 2007, 127, 44-46.	0.3	3
107	Nanoscale Evaluation of Structure and Surface Potential of Gated Field Emitters by Scanning Maxwell-Stress Microscope. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 6912-6915.	0.8	3
108	A regenerative approach for partial tracheal defects, an in vivo canine model. <i>Inflammation and Regeneration</i> , 2007, 27, 570-574.	1.5	3

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109	Fabrication and Characterization of Cross-Edge-Structured Vertical Field Emitter Arrays. Japanese Journal of Applied Physics, 1994, 33, 7171-7175.	0.8	2
110	Charging Damage of Silicon-on-Insulator (SOI) Wafer Determined by Scanning Maxwell-Stress Microscopy. Japanese Journal of Applied Physics, 2001, 40, 2907-2910.	0.8	2
111	Electron Motion Three-Dimensional Confinement for Microelectronic Vacuum Gauges with Field Emitters. Japanese Journal of Applied Physics, 2001, 40, 2165-2172.	0.8	2
112	Close Observation of the Geometrical Features of an Ultranarrow Silicon Nanowire Device. Japanese Journal of Applied Physics, 2002, 41, 4419-4422.	0.8	2
113	P-Channel Vertical Double-Gate MOSFET Fabricated by Utilizing Ion-Bombardment-Retarded Etching Process. Japanese Journal of Applied Physics, 2004, 43, 2156-2159.	0.8	2
114	Emission Statistics for HfC Emitter Arrays after Residual Gas Exposure. Japanese Journal of Applied Physics, 2005, 44, 5959-5963.	0.8	2
115	Design and fabrication of an ultrahigh-luminance field-emission display. Journal of Vacuum Science & Technology B, 2009, 27, 740.	1.3	2
116	Enhancement of ion-induced bending phenomenon using a double-layered film for field emitter array fabrication. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C2C1-C2C4.	0.6	2
117	Integration of thin film transistors and vertical thin film field emitter arrays using ion-induced bending. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 032205.	0.6	2
118	Silicon films on insulator formation using lateral solid-phase epitaxy induced by focused ion beam. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2699.	1.6	1
119	Feasibility of Vacuum Microelectronics Voltage Comparator. Japanese Journal of Applied Physics, 1995, 34, 6219-6221.	0.8	1
120	Emission Characteristics of Amorphous Silicon Field Emitter Arrays Sealed in a Vacuum Package. Japanese Journal of Applied Physics, 1999, 38, 7213-7216.	0.8	1
121	Fabrication technology of Si nanodot nanowire memory transistors using an inorganic EB resist process. , 0, , .		1
122	Oscillator Ionization Vacuum Gauge with Field Emitters. Japanese Journal of Applied Physics, 2002, 41, 5945-5950.	0.8	1
123	Programmable Conductivity of Silicon Nanowires with Side Gates by Surface Charging. Japanese Journal of Applied Physics, 2003, 42, 2422-2425.	0.8	1
124	Current Status of Vacuum Microelectronics. IEEJ Transactions on Fundamentals and Materials, 2003, 123, 425-428.	0.2	1
125	Development of a CdTe x-ray imaging device driven by a vertical thin film field emission array. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C2D22-C2D25.	0.6	1
126	Ion induced bending (IIB) phenomenon for 3-D structure fabrication. Surface and Coatings Technology, 2011, 206, 775-780.	2.2	1

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127	Monolithic integration of Si field emitter arrays with n-MOSFET circuits. , 0, , .		0
128	Silicon nanowire memory using surface charging and its operation analysis by scanning Maxwell-stress microscopy (SMM). , 0, , .		0
129	Electrical and geometrical properties of a Si quantum nanowire device fabricated by an inorganic EB resist process. , 0, , .		0
130	Fabrication of Si FEA integrated with MOSFET driving circuits. , 0, , .		0
131	Modeling of field emission nanotriodes with carbon nanotube emitters. , 0, , .		0
132	Ring-shaped images as a result of non-uniform field emission from capped carbon nanotubes. , 0, , .		0
133	Emission statistics for Si and HfC/Si emitter arrays after gas exposure. , 0, , .		0
134	On the V_{th} controllability for 4-terminal double-gate MOSFETs. , 0, , .		0
135	STM observations of hafnium carbide thin films as a field emission material. , 0, , .		0
136	Low temperature fabrication of poly-Si FEA for display application. , 0, , .		0
137	Work function control of metal gates by interdiffused Ni-Ta with high thermal stability. , 0, , .		0
138	Doping integrity diagnostics of planar transistor channel structures by scanning nonlinear dielectric microscopy. Journal of Vacuum Science & Technology B, 2006, 24, 237.	1.3	0
139	Determination of the best conditions of scaffolds for tissue engineered canine skull regeneration. Laryngoscope, 2009, 119, S257.	1.1	0
140	10.2: Integration of TFT and VTF-FEA using ion-induced bending. , 2010, , .		0
141	Densification of spin-on-glass (SOC) film by RF plasma treatment. IOP Conference Series: Materials Science and Engineering, 2011, 18, 032007.	0.3	0